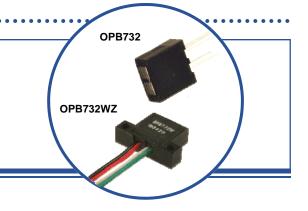
Long Distance Reflective Switch OPB732, OPB732WZ



Features:

- PC board mounting (OPB732)
- 24" (610 mm) 26 AWG wired with mounting tabs (OPB732WZ)
- Non-contact infrared switch
- Up to 1" or more reflective distance depending on circuitry

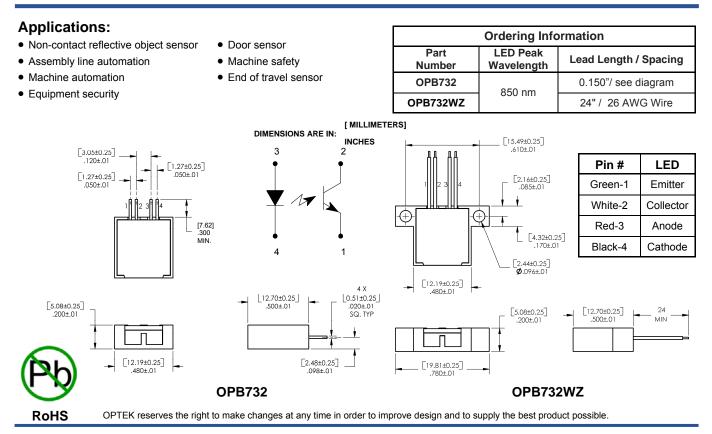


Description:

OPB732 uses an Infrared LED and Phototransistor in a reflective switch configuration. The assembly is offered with either PCBoard through hole pins (**OPB732**) or 24" (610 mm), 26 AWG wires (**OPB732WZ**), and uses an opaque housing to reduce the sensor's ambient light sensitivity. The emitter and sensor are protected by a clear window, providing a device that can operate in a dusty environment. The phototransistor can be configured as a Common Collector or Common Emitter device.

While an object is in the reflective path of the device, light from the LED will be reflected back to the housing irradiating the surface (base) of the phototransistor. When Infrared light strikes the phototransistor, the transistor becomes forward biased and is considered to be in the "ON" state, providing an $I_{C(ON)}$ current proportional to the light striking the phototransistor. With the Infrared light from the LED not being reflected to the phototransistor, the phototransistor, the phototransistor turns "OFF," minimizing the $I_{C(ON)}$ current.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.



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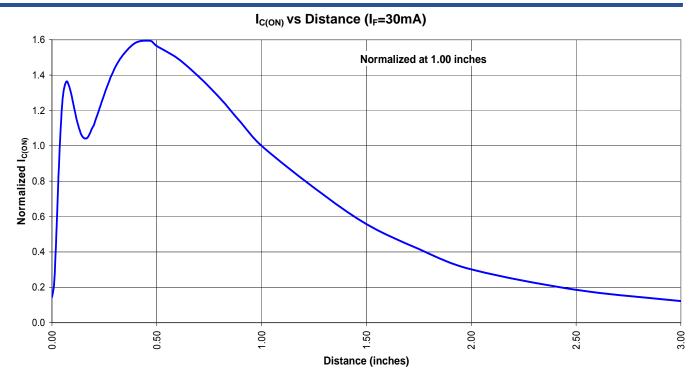


Storage Temperature						-40° C to +100°
Operating Temperature						-40° C to +85°
Lead Soldering Temperature (1/16" (1.6mm) from case for 5 seconds with soldering iron) ⁽²⁾						
LED						3 ····,
Forward Current						50 m
Peak Forward current (2 µs pulse width, 0.1% Duty Cycle)						1
Reverse DC Voltage						3
Power Dissipation						100 m\
	oto Transistor					
Collector-Emitter Voltage						30
Collector DC Current						50 m
Power Dissipation						100 m\
Electrical	Characteristics (T _A = 25°C unless	otherw	vise no	ted)		
SYMBOL	PARAMETER	ΜΙΝ	ТҮР	МАХ	UNITS	CONDITIONS
Input LED (See OP265 for additional information, refe	rence c	only)		I	
V _F	Forward Voltage	-	-	1.8	V	I _F = 20 mA
I _R	Reverse Current	-	-	100	μA	V _R = 2 V
Output Pho	totransistor (See OP505 for additional inf	ormatio	on, refe	rence o	nly)	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_{\rm C}$ = 100 µA, E _E = 0 mw/cm ²
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V_{CE} = 10 V, E _E = 0 mw/cm ²
Coupled						,
V _{CE(SAT)}	Collector-Emitter Saturation Voltage ⁽⁴⁾	-	-	0.4	V	$I_{\rm C}$ = 250 µA, $I_{\rm F}$ = 30 mA , (4)
I _{C(ON)}	On-State Collector Current ⁽⁴⁾	0.25	-	-	mA	V _{CE} = 1 V, I _F = 30 mA, (4)
I _{CX}	Cross Talk	-	-	50	μΑ	V_{CE} = 5 V, I_F = 30 mA, No reflective surface
(2) RM (3) Met chlo	barameters tested using pulse technique. A flux is recommended. Duration can be extend hanol or isopropanol are recommended as clear prinated hydrocarbons and keytones. ance = 1" (from front of package to a 90% diffu	ning age	ents. Th	e plastic		

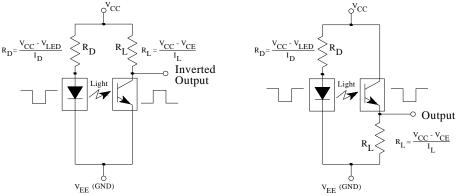
OPTEK reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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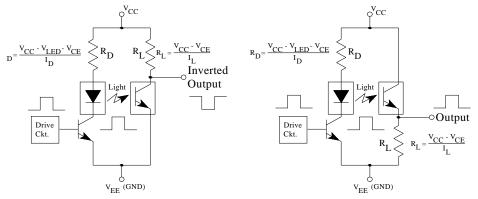








Pulsed—Drive Circuit for LED & Phototransistor



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